

ABSTRACT OF THE DISCLOSURE

Wet etching is performed on a storage electrode (7) made of ruthenium from above using periodic acid or a cerium ammonium nitrate solution. By using that kind of etching liquid, ruthenium as well as oxide films formed on the surface of the storage electrode (7) can be etched, causing the surface of the storage electrode (7) to be entirely etched. As a result, needle projections having been formed on the top surface of the storage electrode (7) are removed, rounding the top ends of the storage electrode (7). Consequently, the thickness of a dielectric film of a DRAM capacitor to be formed on the storage electrode (7) can be easily made uniform, allowing a reduction in leakage current 10 of the capacitor.